Abstracts

Influence of output impedance on power added efficiency of Si-bipolar power transistors

F. van Rijs, R. Dekker, H.A. Visser, H.G.A. Huizing, D. Hartskeerl, P.H.C. Magnee and R. Dondero. "Influence of output impedance on power added efficiency of Si-bipolar power transistors." 2000 MTT-S International Microwave Symposium Digest 00.3 (2000 Vol. III [MWSYM]): 1945-1948.

The power added efficiency (PAE) of low voltage RF bipolar power transistors for cellular applications, is carefully analyzed experimentally and theoretically. We found that the transistor with low output capacitance operates in "inverse class AB", which facilitates high efficiencies. FE as high as 77% at 1.8 GHz with 3.5 V supply voltage have been obtained.

❑ Return to main document.